

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet

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of

27

Application Number

10/686,795

Filing Date

October 16, 2003

First Named Inventor

Joseph J. Sumakeris

Group Art Unit

2811

Examiner Name

Cuong Quang Nguyen

Attorney Docket Number

5308-248

U.S. PATENTS AND PATENT PUBLICATIONS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
es	4	Baranov et al., "EPR Study of Shallow and Deep Phosphorous Centers in 6H-SiC," Physical Review B66, 2002, pp. 165206-1 through 165206-7	
ca	5	Rashid et al., "Trench Oxide Protection for 10 kV 4H-SiC Trench MOSFETs," Power Electronics and Drive Systems, 2003, Vol. 2, pp. 1354-1358	
Oh	6	Sugawara et al., "12-19kV 4H-SiC pin Diodes with Low Power Loss," Proceedings of 2001 International Symposium on Power Semiconductor Devices & Ics, Osaka, pp. 27-30	
Ch	7	Notification of Transmittal of the International Search Report and the Written Opinion of the International Searching Authority, or the Declaration, PCT/US2004/031883, January 7, 2005	

Examiner Signature

Date Considered

3-16-05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiner Name

Cuong Q. Nguyen

Attorney Docket Number

5308-286

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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			

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Sheet	1	of	1
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Attorney Docket Number	5308-286

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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
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10-16-03

Substitute form 1449A/PTO		Complete if Known 10/686795	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	To Be Assigned
		Filing Date	Concurrently Herewith
		First Named Inventor	Joseph John Sumakeris
		Group Art Unit	
		Examiner Name	
Sheet 1 of 1	Attorney Docket Number	5308-2861	

U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
Ch	1	US-6,472,677	B1	Rodriguez et al.	10-29-2002
Ch	2	US-6,403,982	B2	Carter, Jr. et al.	06-11-2002
Ch	3	US-6,396,080	B2	Carter, Jr. et al.	05-28-2002
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Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
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Ch	23	Heissenstein et al., "Characterization of phosphorus doped <i>n</i> -type 6 <i>H</i> -silicon carbide epitaxial layers produced by nuclear transmutation doping," Journal of Applied Physics, Volume 83, Number 12, pp. 7542-7546, 15 June 1998		

Examiner Signature	<i>Ch</i>	Date Considered	03-16-05
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